



P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
- 30	0.0075 at $V_{GS} = - 10$ V	- 15
	0.011 at $V_{GS} = - 4.5$ V	- 12.3

FEATURES

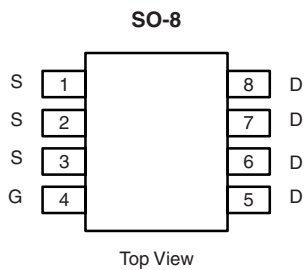
- TrenchFET[®] Power MOSFET



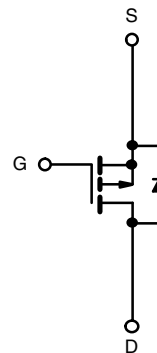
RoHS
COMPLIANT

APPLICATIONS

- Notebook
 - Load switch
 - Battery switch



Ordering Information: Si4413ADY-T1-E3 (Lead (Pb)-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	10 sec	Steady State	Unit	
Drain-Source Voltage	V_{DS}	- 30		V	
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	- 15	- 10.5	A
		$T_A = 70$ °C	- 11.8	- 8.3	
Pulsed Drain Current	I_{DM}	- 50		A	
Continuous Source Current (Diode Conduction) ^a	I_S	- 2.7	- 1.36		
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	3.0	1.5	W
		$T_A = 70$ °C	1.9	0.95	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	33	42	°C/W
		Steady State	70	84	
Maximum Junction-to-Foot (Drain)	R_{thJF}	16	21		

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.



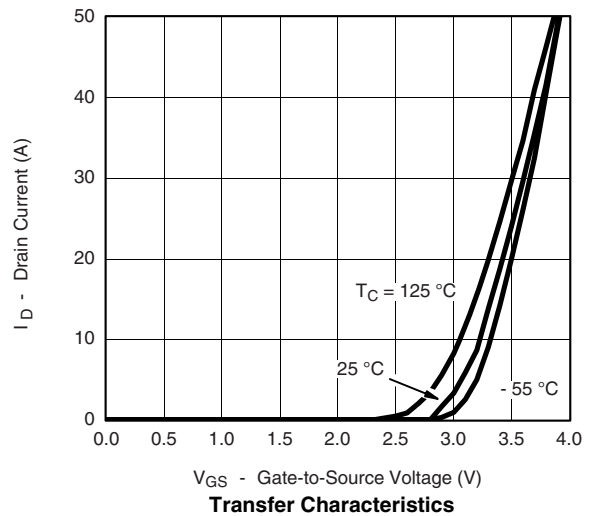
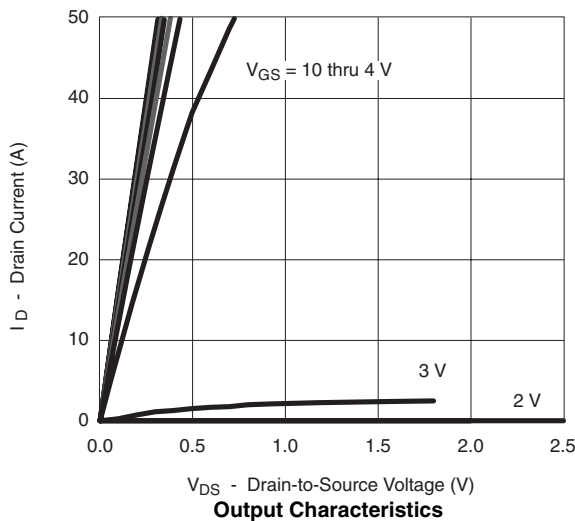
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1.0		-3.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	-30			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -13\text{ A}$		0.0063	0.0075	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -10\text{ A}$		0.0083	0.011	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -13\text{ A}$		50		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -2.7\text{ A}, V_{GS} = 0\text{ V}$		-0.74	-1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -5\text{ V}, I_D = -13\text{ A}$		61	95	nC
Gate-Source Charge	Q_{gs}		15.5			
Gate-Drain Charge	Q_{gd}		32			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_G = 6\text{ }\Omega$		21	35	ns
Rise Time	t_r		18	30		
Turn-Off Delay Time	$t_{d(off)}$		170	260		
Fall Time	t_f		97	150		
Gate Resistance	R_g			3.4		
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -2.1\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		70	110	ns

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

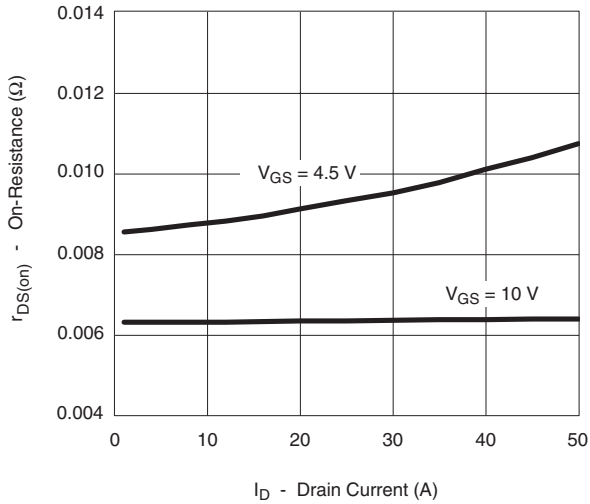
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted

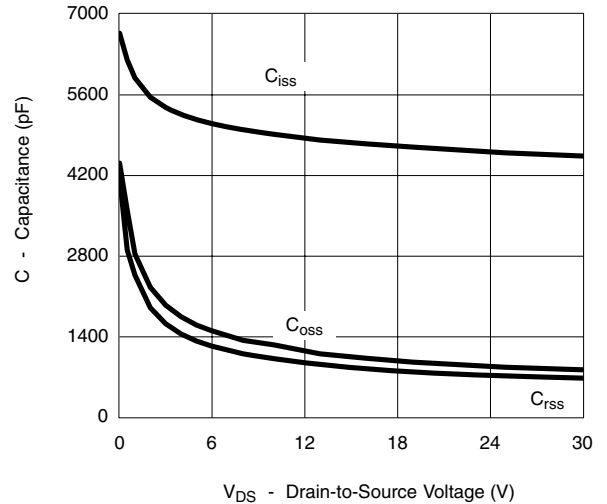




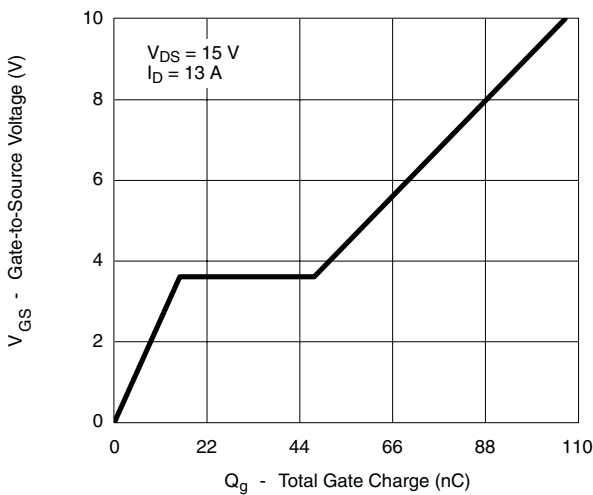
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



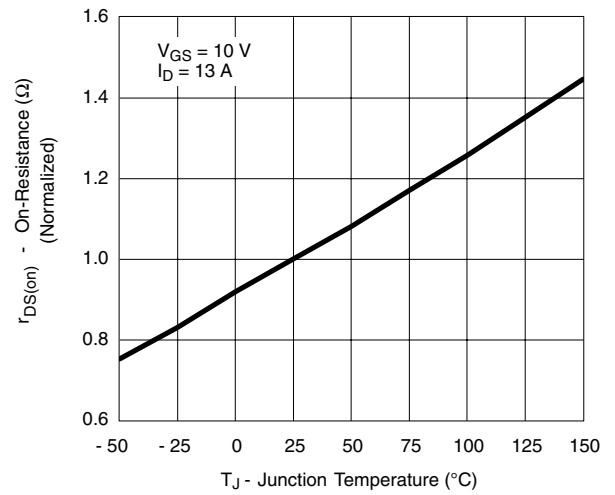
On-Resistance vs. Drain Current



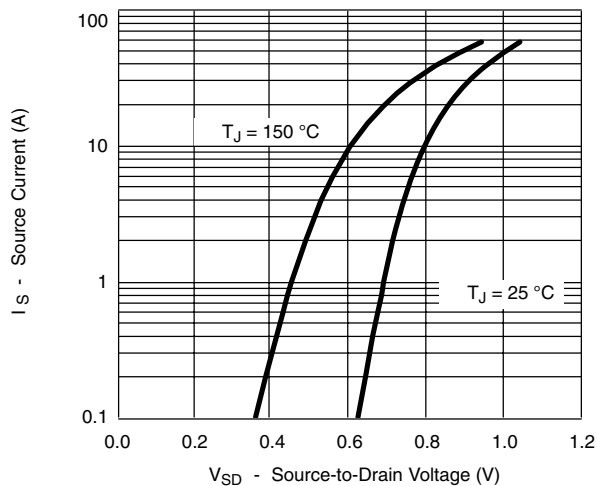
Gate Charge



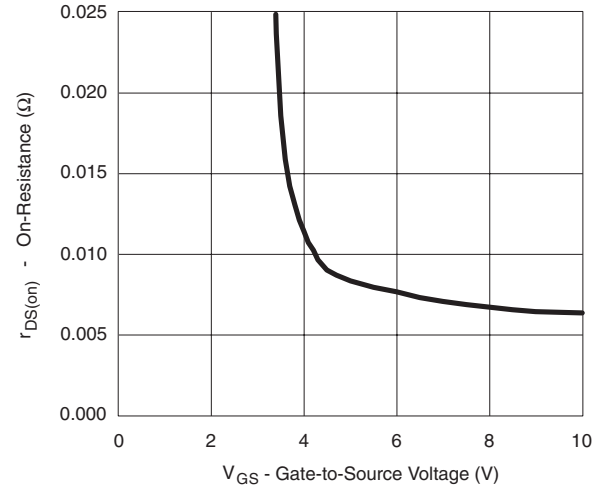
Source-Drain Diode Forward Voltage



Capacitance



On-Resistance vs. Junction Temperature



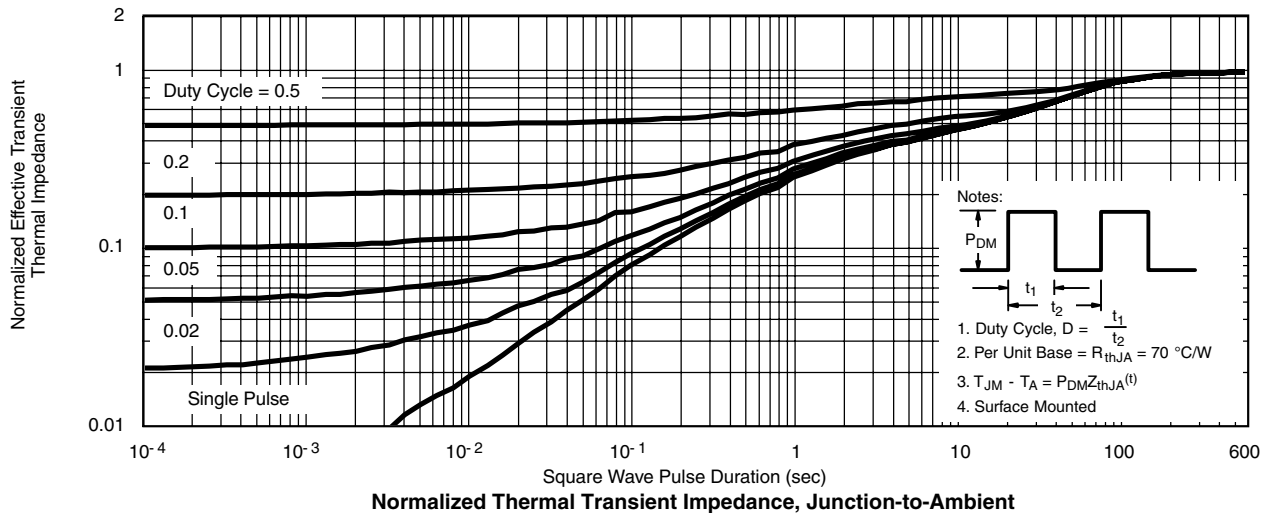
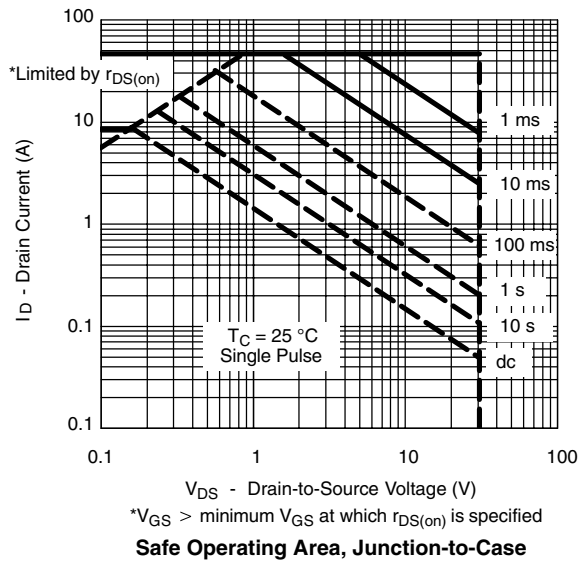
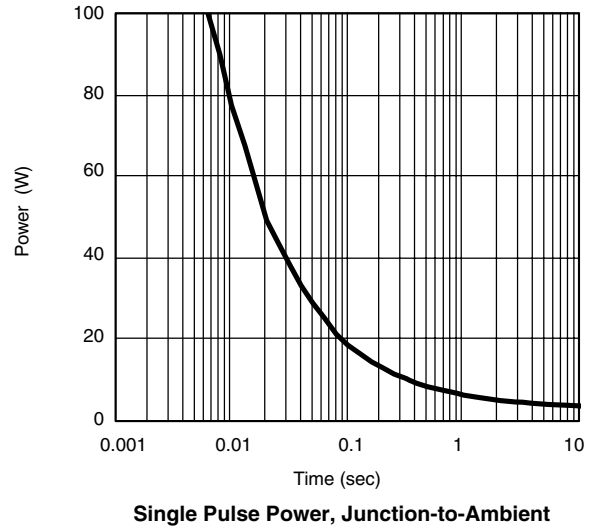
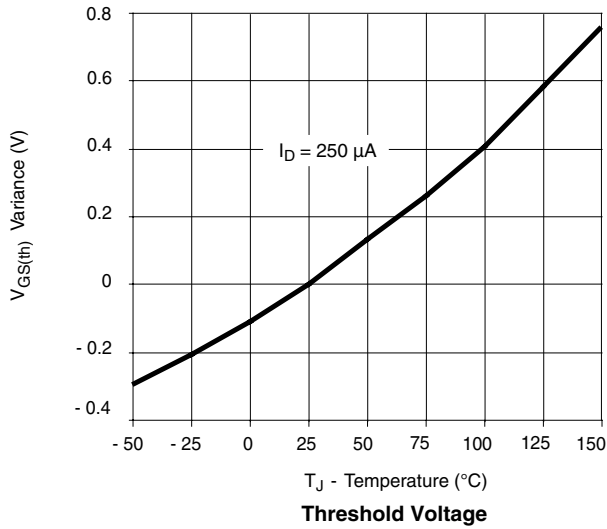
On-Resistance vs. Gate-to-Source Voltage

Si4413ADY

Vishay Siliconix

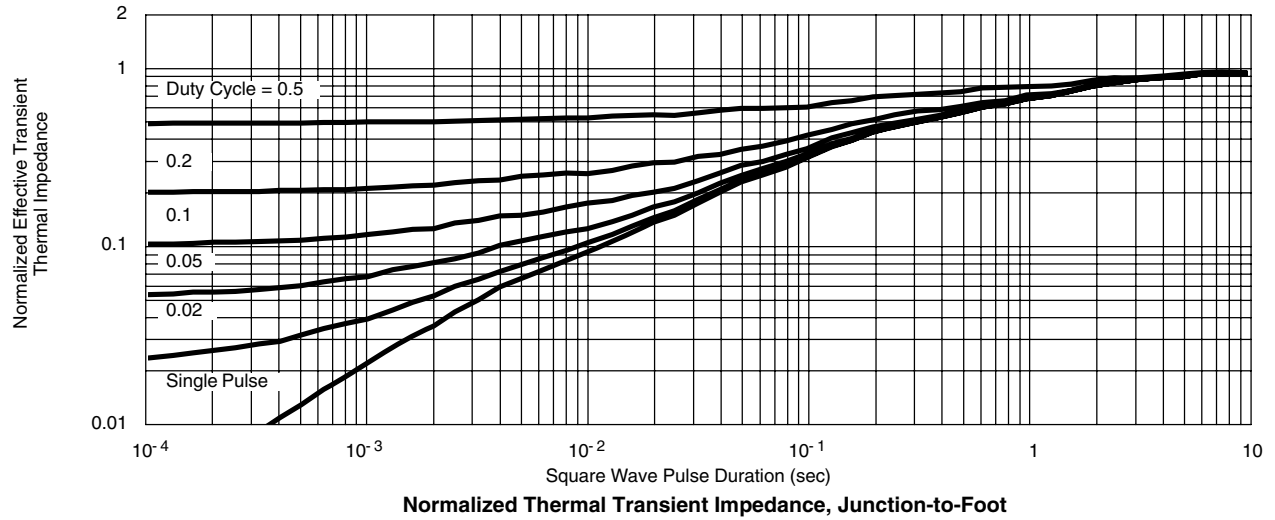


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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